

Rectifier diode ultrafast

Rev. 01 — 16 October 2007

Product data sheet

1. Product profile

1.1 General description Ultrafast, epitaxial rectifier diode in a SOD59 (TO-220AC) plastic package. **1.2 Features** Low thermal resistance Fast switching Soft recovery characteristic Low forward voltage drop Low switching loss High thermal cycling performance W.DZSC.COM **1.3 Applications** Discontinuous Current Mode (DCM) Output rectifiers in high frequency switched-mode power supplies Power Factor Correction (PFC) 1.4 Quick reference data V_{RRM} ≤ 600 V I_{F(AV)} ≤ 15 A V_F ≤ 1.2 V t_{rr} ≤ 60 ns

2. Pinning information

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k — — — a 001aaa020
nb	mounting base; cathode	ک ک	
		1 2	
		SOD59 (2-lead TO-220A	(C)





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3. Ordering information

Table 2. Ordering information						
Type number	Package	e				
	Name	Description	Version			
BYT79-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

4. Limiting values

Table 3.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Symbol	Falalletel	Conditions	IVIIII	IVIDA	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	square waveform; δ = 1.0; T _{mb} \leq 147 °C	-	600	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; T _{mb} \leq 108 °C	-	15	A
I _{FRM}	repetitive peak forward current	t = 25 $\mu s;$ square waveform; δ = 0.5; $T_{mb} \leq$ 108 $^{\circ}C$	-	30	A
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	130	А
		t = 8.3 ms; sinusoidal waveform	-	143	А
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C
-					

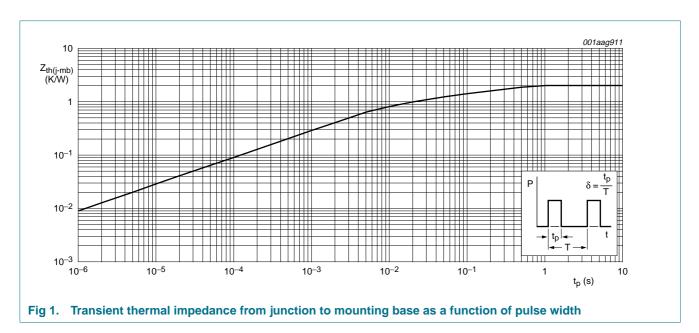
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Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; see <u>Figure 1</u>	-	-	2.0	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

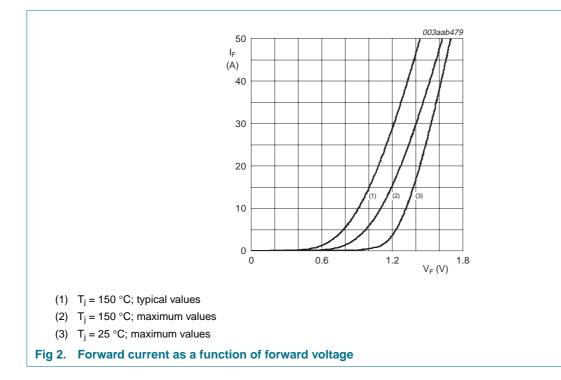




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6. Characteristics

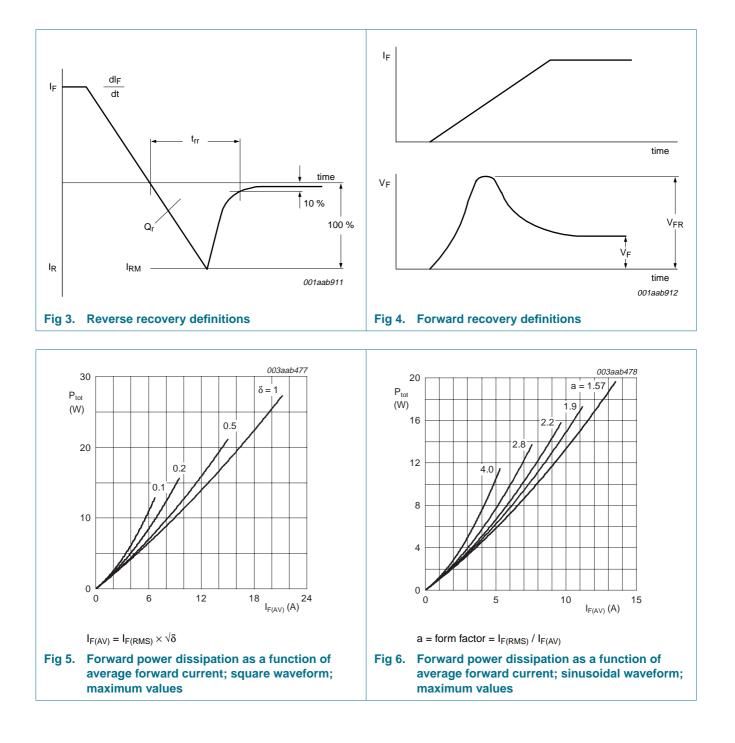
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
VF	forward voltage	I _F = 15 A; T _j = 150 °C; see <u>Figure 2</u>	-	1.0	1.2	V
		I _F = 15 A; see <u>Figure 2</u>	-	1.17	1.38	V
I _R	reverse current	V _R = 600 V	-	5	50	μA
		V_R = 600 V; T_j = 100 °C	-	0.2	0.8	mA
Dynamic of	characteristics					
Qr	recovered charge	$I_F = 2 \text{ A to } V_R \ge 30 \text{ V}; \text{ d}_F/\text{d}t = 20 \text{ A}/\mu\text{s};$ see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 A \text{ to } V_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s}; \text{ see } Figure 3$	-	50	60	ns
I _{RM}	peak reverse recovery current	$\label{eq:l_F} \begin{array}{l} I_F = 10 \ A \ to \ V_R \geq 30 \ V; \\ dI_F/dt = 50 \ A/\mu s; \ T_j = 100 \ ^\circ C; \\ see \ \underline{Figure \ 3} \end{array}$	-	3.0	5.2	A
V _{FR}	forward recovery voltage	$I_F = 10 \text{ A}; \text{ dI}_F/\text{dt} = 10 \text{ A}/\mu\text{s};$ see Figure 4	-	3.2	-	V



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7. Package outline

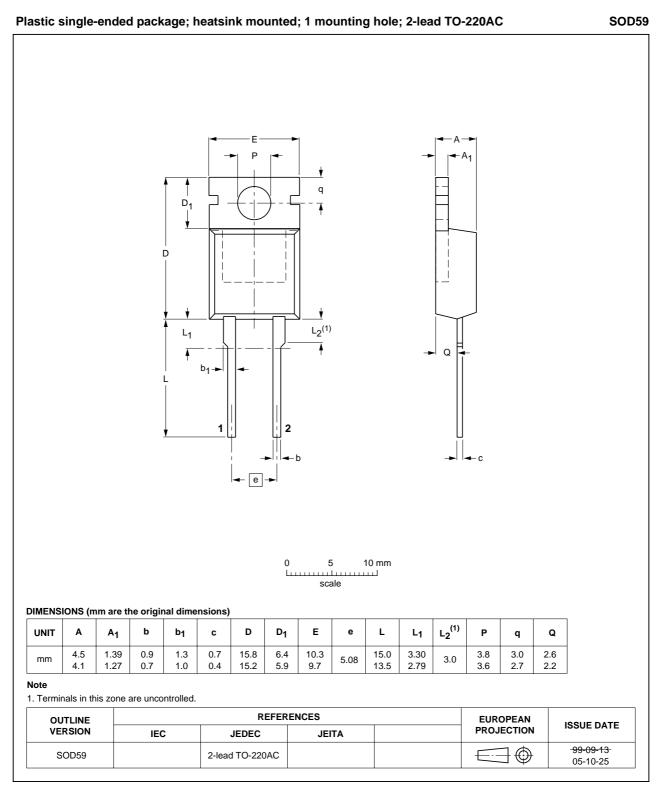


Fig 7. Package outline SOD59 (2-lead TO-220AC)

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8. Revision history

Table 6.	6. Revision history				
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BYT79-600	_1	20071016	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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